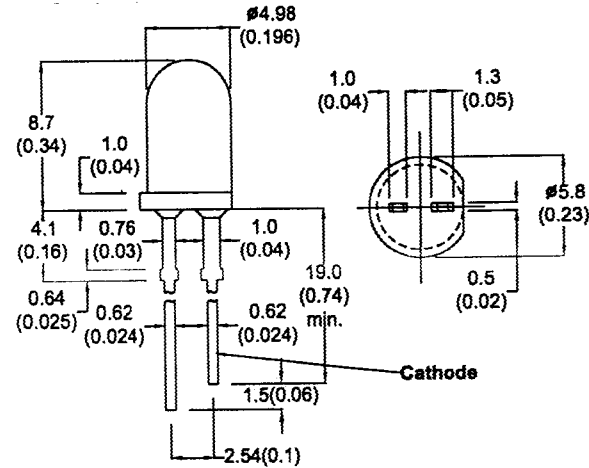


MICRO

MI51TA-2
MI51TA-3
INFRARED
EMITTING
DIODE

DESCRIPTION

MI51TA-2 & MI51TA-3 is GaAlAs infrared emitting diode molded in T-1 3/4 standard 5mm diameter clear transparent lens.



- All Dimension in mm (inch)
- No Scale
- Tol. : + / - 0.3mm

ABSOLUTE MAXIMUM RATING (Ta=25°C)

Forward Current (Continuous)

Pulse Forward Current

Reverse Voltage (Continuous)

Power Dissipation

Operating Temperature Range

Lead Soldering Temperature (1/16" from body)

MI51TA-2

100mA

1A*

5V

200mW

MI51TA-3

100mA

1A*

5V

230mW

-25 to +85°C

260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER		SYMBOL	MI51TA-2	MI51TA-3	UNIT	CONDITIONS
Radiant Power Output	Min	Po	0.6	0.8	mW	IF=20mA
	Typ		1.0	1.5		
Forward Voltage	Typ	VF	1.7	1.6	V	IF=20mA
	Max		2.0	2.3		
Reverse Current	Max	IR	100	100	μA	VR=5V
Peak Wavelength	Typ	λp	770	830	nm	IF=20mA
Spectrum Line Half Width	Typ	Δλ	30	32	nm	IF=20mA
Viewing Angle	Typ	2 θ 1/2	75	75	dagree	IF=20mA



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